

Silicon Power Transistors

2SC2485

DESCRIPTION

- With TO-3PN package
- Complement to type 2SA1061
- High collector power dissipation

APPLICATIONS

- High power audio frequency amplifier

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

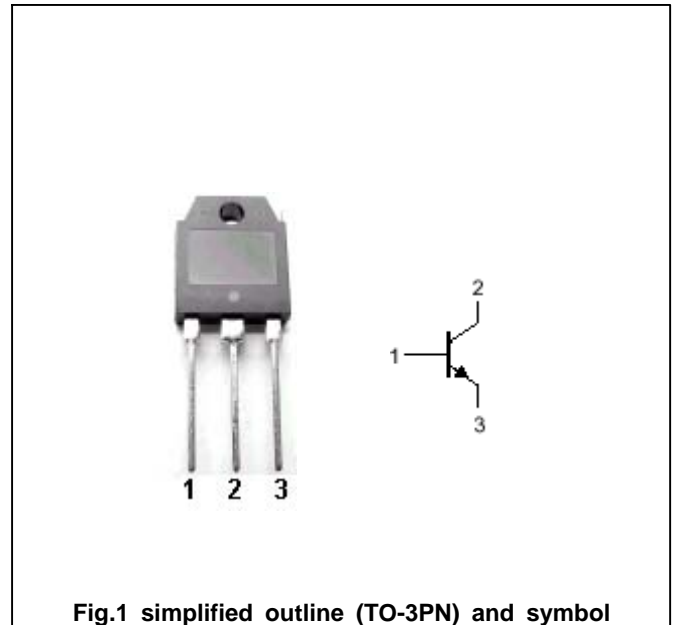


Fig.1 simplified outline (TO-3PN) and symbol

LIMITING VALUES

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	100	V
V_{CEO}	Collector-emitter voltage	Open base	100	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current (DC)		6	A
I_{CP}	Collector current (Pulse)		10	A
P_C	Collector power dissipation	$T_C=25$	70	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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2SC2485**CHARACTERISTICS**T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A I _B =0.4A			2.0	V
V _{BE}	Emitter-base on voltage	I _C =4A; V _{CE} =5V			1.8	V
I _{CBO}	Collector cut-off current	V _{CB} =100V I _E =0			50	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =3V; I _C =0			50	μ A
h _{FE-1}	DC current gain	I _C =0.2A ; V _{CE} =5V	20			
h _{FE-2}	DC current gain	I _C =1A ; V _{CE} =5V	40		200	
h _{FE-3}	DC current gain	I _C =4A ; V _{CE} =5V	20			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =5V		20		MHz

◆ **h_{FE-2} Classifications**

R	Q	P
40-80	60-120	100-200

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PACKAGE OUTLINE

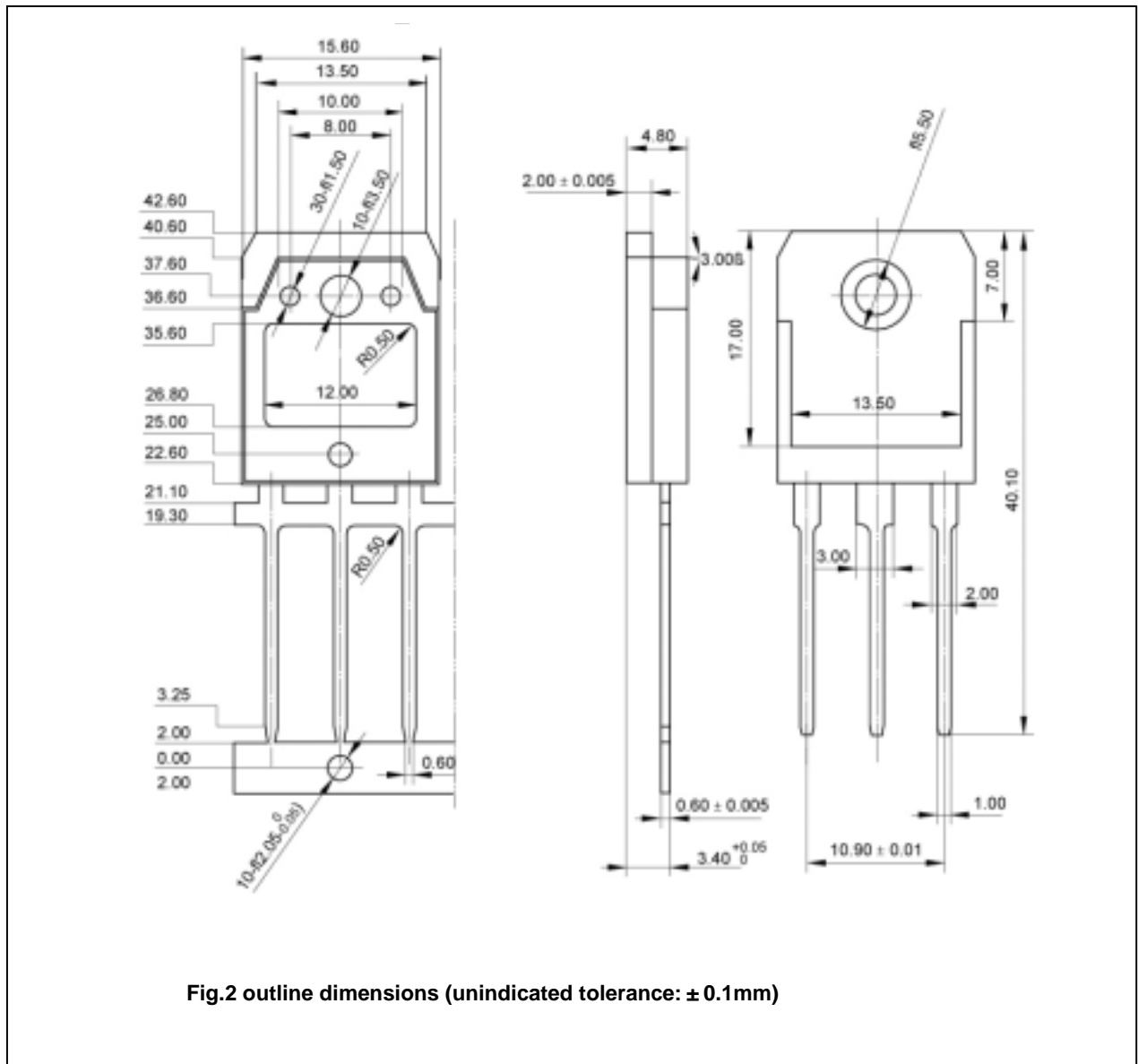


Fig.2 outline dimensions (unindicated tolerance: ± 0.1mm)